

**Amendments to the Claims**

This listing of claims will replace all prior versions and listings of claims in the application.

1-67 (cancelled).

68 (currently amended). A method of forming a gallium nitride semiconductor structure comprising:

converting a surface of a silicon substrate to a silicon-based compound to form a converted surface;

forming a buffer layer comprising aluminum and nitrogen on the converted surface; and

forming a gallium nitride region on the buffer layer including laterally growing at least a portion of the gallium nitride region.

69 (previously presented). The method of claim 68, further comprising forming a device in the gallium nitride region.

70 (previously presented). The method of claim 69, further comprising forming a device in the silicon substrate.

71 (previously presented). The method of claim 68, wherein at least a portion of the gallium nitride region has a defect density of less than  $10^9 \text{ cm}^{-2}$ .

72 (previously presented). The method of claim 71, wherein the portion of the gallium nitride region having a defect density of less than  $10^9 \text{ cm}^{-2}$  extends continuously over the substrate.

73 (previously presented). The method of claim 68, wherein at least a portion of gallium nitride region extends continuously over the substrate.

74 (previously presented). The method of claim 68, wherein buffer layer comprises aluminum nitride.

75. (previously presented) The method of claim 68, wherein the substrate is a bulk silicon substrate.

76 (previously presented). The method of claim 68, wherein the substrate is an SOI substrate.

77 (previously presented). The method of claim 68, wherein the substrate is a SIMOX substrate.

78 (previously presented). The method of claim 68, comprising converting the entire surface of the silicon substrate to the silicon-based compound.

79 (previously presented). The method of claim 68, wherein the gallium nitride region has a thickness of between about 0.5 and about 2.0 micron.

80 (previously presented). The method of claim 68, wherein the silicon-based compound is silicon carbide.

81 (cancelled).

82 (previously presented). The method of claim 68, wherein the step of forming the gallium nitride region on the buffer layer includes vertically growing at least a portion of the gallium nitride region.

83 (previously presented). The method of claim 68, comprising forming the buffer layer comprising aluminum and nitrogen directly on the converted surface.

84 (previously presented). The method of claim 68, comprising forming the gallium nitride region directly on the buffer layer.

Serial No. 10/633,952

85 (new). The method of claim 68, wherein the buffer layer has a thickness greater than the thickness of the converted surface.